

GE75N07

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BV _{DSS}	75V
R _{DS(ON)}	11mΩ
I _D	80A

Description

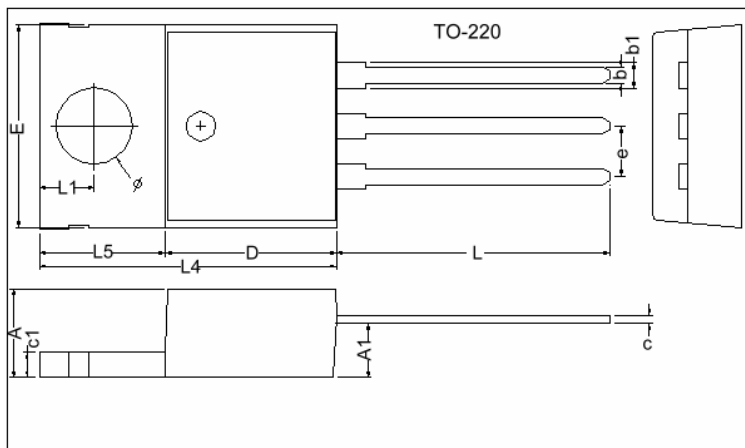
The GE75N07 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The through-hole version (TO-220) is available for low-profile applications and suited for low voltage applications such as DC/DC converters.

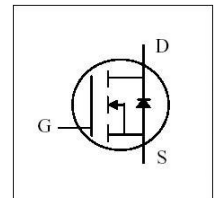
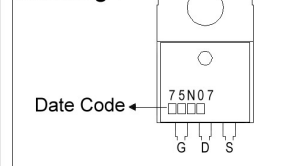
Features

- *Low Gate Charge
- *Simple Drive Requirement
- *Fast Switching Characteristics
- *RoHS Compliant

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	Ø	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	75	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current, V _{GS} @10V	I _D @T _C =25°C	80	A
Continuous Drain Current, V _{GS} @10V	I _D @T _C =100°C	56	A
Pulsed Drain Current ¹	I _{DM}	300	A
Total Power Dissipation	P _D @T _C =25°C	156	W
Linear Derating Factor		0.125	W/°C
Single Pulse Avalanche Energy ³	E _{AS}	450	mJ
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	R _{thj-case}	0.8	°C/W
Thermal Resistance Junction-ambient Max.	R _{thj-amb}	62	°C/W

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	75	-	-	V	V _{GS} =0, I _D =1mA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.08	-	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} =V _{GS} , I _D =250uA
Forward Transconductance	g _{fs}	-	40	-	S	V _{DS} =10V, I _D =40A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	10	uA	V _{DS} =60, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		-	-	100	uA	V _{DS} =75V, V _{GS} =0
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	11	mΩ	V _{GS} =10V, I _D =40A
Total Gate Charge ²	Q _g	-	83	130	nC	I _D =40A V _{DS} =60V V _{GS} =4.5V
Gate-Source Charge	Q _{gs}	-	10	-		
Gate-Drain ("Miller") Change	Q _{gd}	-	51	-		
Turn-on Delay Time ²	T _{d(on)}	-	15	-	ns	V _{DS} =40V I _D =30A V _{GS} =10V R _G =10Ω R _D =1.33Ω
Rise Time	T _r	-	73	-		
Turn-off Delay Time	T _{d(off)}	-	340	-		
Fall Time	T _f	-	200	-		
Input Capacitance	C _{iss}	-	4270	6830	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	-	690	-		
Reverse Transfer Capacitance	C _{rss}	-	320	-		
Gate Resistance	R _g	-	1.8	2.7	Ω	f=1.0MHz

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	1.5	V	I _S =40A, V _{GS} =0V, T _j =25°C
Reverse Recovery Time	T _{rr}	-	90	-	ns	I _S =40A, V _{GS} =0V di/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	235	-	nC	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

3. Starting T_j=25°C, V_{DD}=50V, L=1mH, R_G=25Ω, I_{AS}=30A.

Characteristics Curve

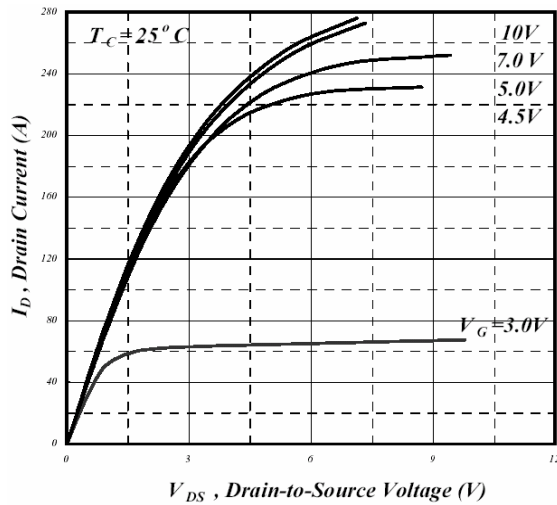


Fig 1. Typical Output Characteristics

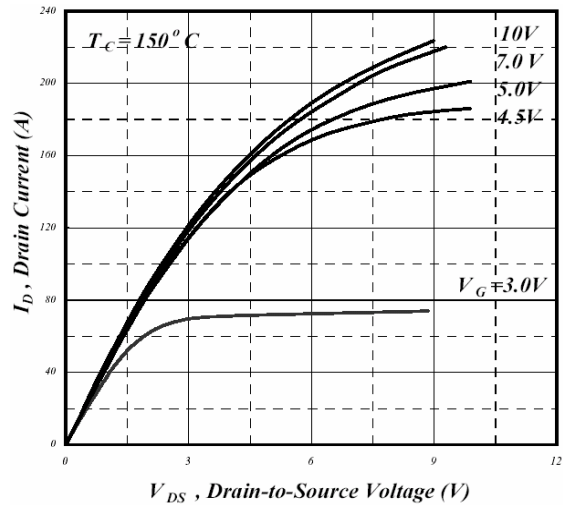


Fig 2. Typical Output Characteristics

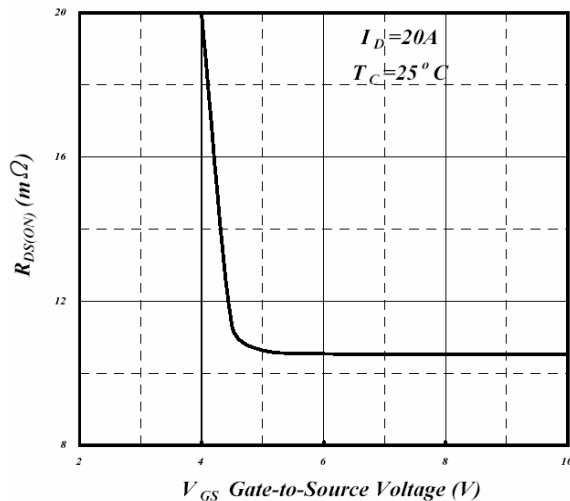


Fig 3. On-Resistance v.s. Gate Voltage

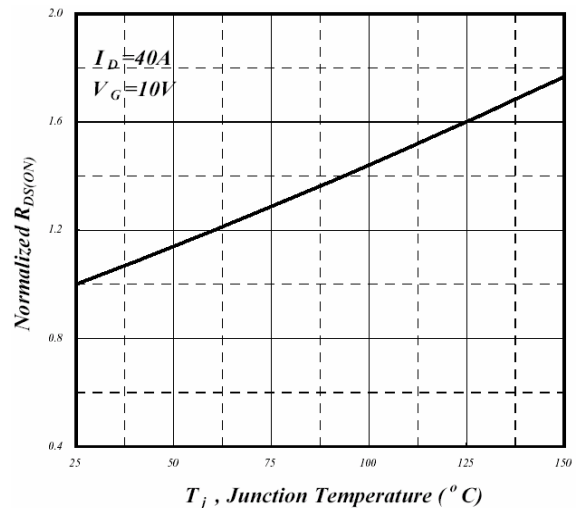


Fig 4. Normalized On-Resistance v.s. Junction Temperature

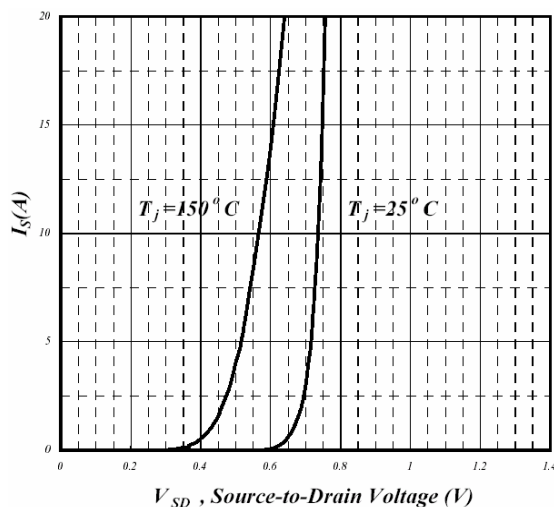


Fig 5. Forward Characteristics of Reverse Diode

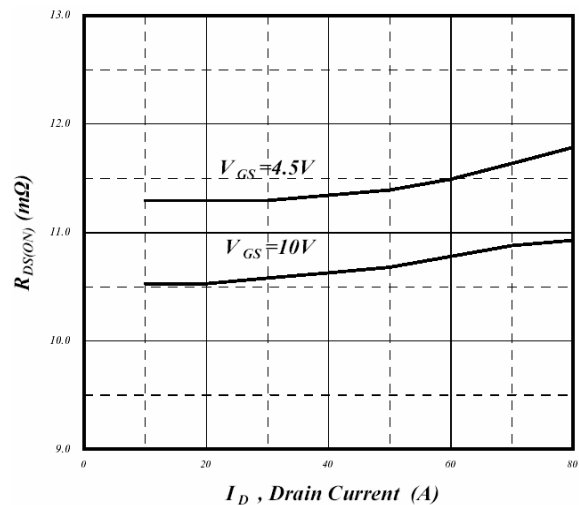


Fig 6. On-Resistance v.s. Drain Current

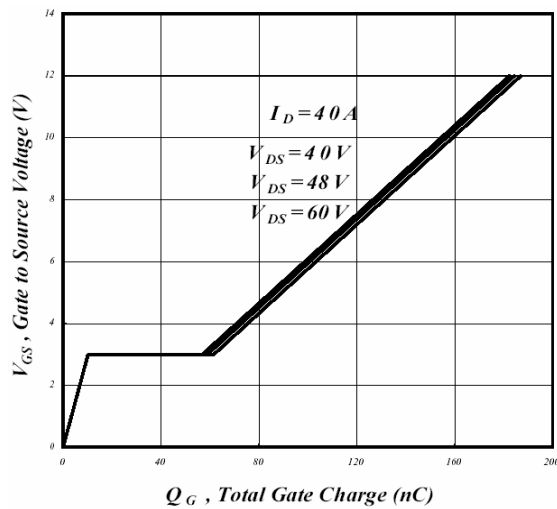


Fig 7. Gate Charge Characteristics

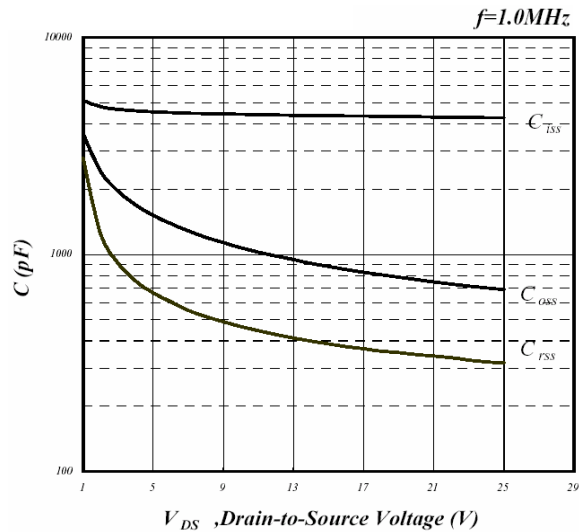


Fig 8. Typical Capacitance Characteristics

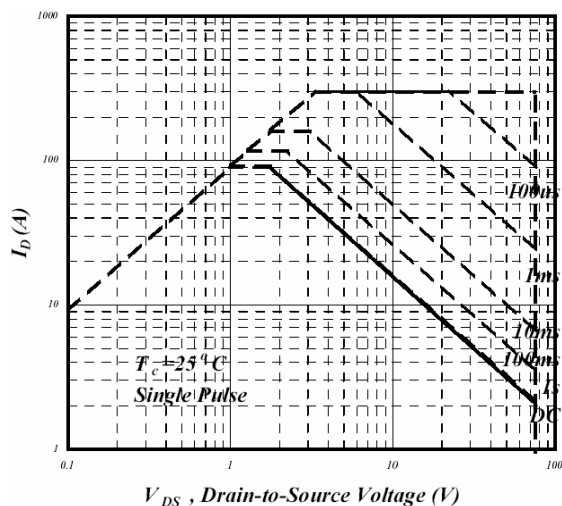


Fig 9. Maximum Safe Operating Area

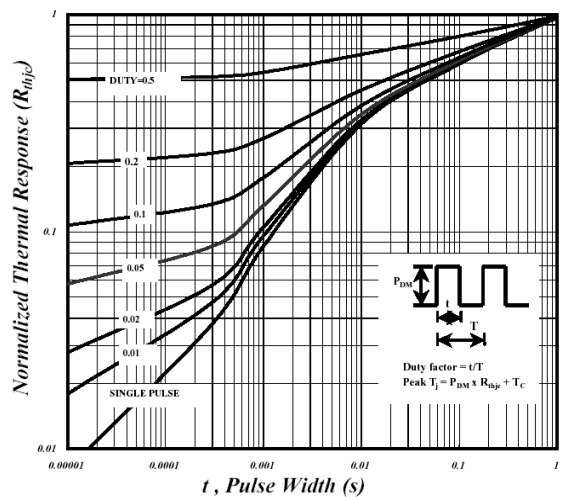


Fig 10. Effective Transient Thermal Impedance

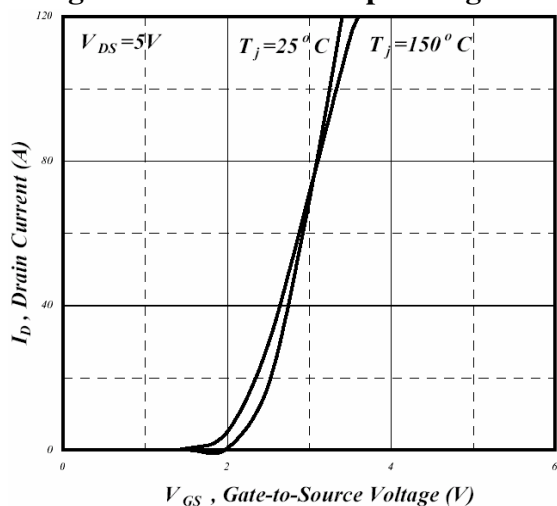


Fig 11. Transfer Characteristics

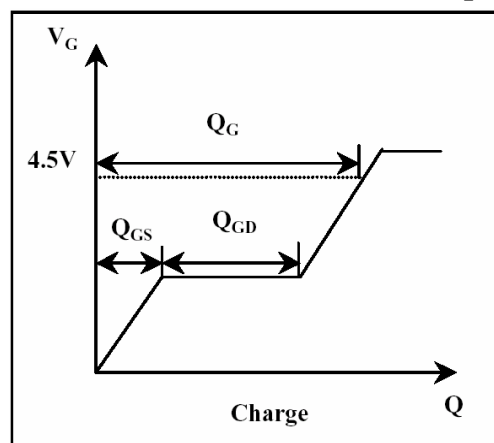


Fig 12. Gate Charge Waveform

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